

ABSTRACT

A semiconductor device has a contact section formed in an interlayer dielectric layer, a first wiring formed over the interlayer dielectric layer and disposed with a separation from the contact section shorter than a specified separation, and a second wiring having a connection region to be connected to the contact section. The connection region has a shape that covers at least the contact section and preferably has a square shape. The second wiring has extension sections extending in non-wiring regions in the connection region to be connected to the contact section. The extension sections are disposed on sides of the connection region other than sides thereof facing the first wiring.

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